Amendments to the Specification

Please replace the paragraph that begins on page 3, line 34 and ends on page 4, line 7, with the following amended paragraph:

A pn-junction is present between the drain area 50, 52, 54 on the one hand and adjacent areas of the epitaxial layer 20 on the other. A space charge zone or a depletion zone forms ~~thereat the thickness or expansion of which~~ there. The thickness or expansion of the space charge or depletion zone that is perpendicular to the pn-junction is dependent on the ~~height~~ magnitude of the applied drain voltage or on a potential difference between the drain area 50, 52, 54 on the one hand and the substrate 10 on the other hand. The reverse-biased pn-junction between the drain area 50, 52, 54 and the substrate 10 ~~in~~ at the same time forms a capacitor whose ~~capacity~~ capacitance is dependent on the thickness of the mentioned space charge zone, and thus on the drain voltage.

Please replace the paragraph that begins on page 4, line 9 with the following amended paragraph:

As already mentioned above, the output ~~capacity~~ capacitance, which is dependent on the drain ~~voltage~~ voltage, or the ~~capacity~~ capacitance between the drain area 50, 52, 54 and the substrate ~~10~~ 10, complicates the matching of a circuit therewith, which is connected to the field effect transistor. Previously, this output ~~capacity~~ capacitance of the field effect ~~transistor~~ transistor, which is dependent on the drain ~~voltage~~ voltage, had to be ~~put up with~~ tolerated.

Please replace the paragraph that begins on page 4, line 20 with the following amended paragraph:

It is the object of embodiments of the present invention to provide a field effect transistor ~~with a capacity~~ having a capacitance that is substantially independent of the drain voltage between a drain area and a substrate.

Please replace the paragraph that begins on page 4, line 20 with the following amended paragraph:

A substantial advantage of the present invention is that from a predetermined minimum drain voltage on, at which the space charge zones, as mentioned, completely fill both the columns or lamellae of the area and the substrate material in their surroundings, a spatial expansion and in particular the thickness of this depletion zone is substantially only dependent on the geometry of these columns or lamellae and no longer on the drain voltage. The ~~capacity~~ capacitance between the drain area and the substrate is then largely independent of the drain voltage. This enables simple, inexpensive, and efficient high-frequency matching of a circuit in which the inventive field effect transistor is used to the field effect transistor.